

ABSTRACT OF THE DISCLOSURE

5

A method for producing a support for epitaxy comprises forming a layer of insulating monocrystalline silicon carbide or insulating monocrystalline gallium nitride in a first substrate of conducting

10 monocrystalline silicon carbide or gallium nitride. The method also comprises transfer of said monocrystalline layer of silicon carbide or gallium nitride onto a second substrate formed from a polycrystalline ceramic material having thermal conductivity of $1.5 \text{ W.cm}^{-1}.\text{K}^{-1}$ or more.

15 This method enables high performance electronic components to be produced cheaply, in particular for high frequency power applications.